

PINNING LAYER FOR MAGNETIC DEVICES

ABSTRACT

A magnetic device (10) comprises an antiferromagnetic layer (18) which is in direct contact with a ferromagnetic layer (16) for inducing an exchange bias in the ferromagnetic layer (16). Thus, the ferromagnetic layer (16) is pinned by the antiferromagnetic layer (18). The antiferromagnetic layer (18) comprises a compound, from the group of orthoferrites, which is usable at high operating temperatures

FIG 1a